Maximum Ratings (T₁ = 25°C unless otherwise noted)

- 5				
Rating	Symbol	Value	Unit	
Peak Repetitive Off-State Voltage (Note 1)BTA16-600CW3G(Gate Open, Sine Wave 50 to 60 Hz, T ₁ = -40° to 125°C)BTA16-800CW3G		V _{drm} , V _{rrm}	600 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_c = 80^{\circ}$ C)		I _{T (RMS)}	12	A
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T _c = 25°C)		I _{TSM}	125	А
Circuit Fusing Consideration (t = 8.3 ms)		l²t	78	A ² sec
Non-Repetitive Surge Peak Off-State Voltage $(T_j = 25^{\circ}C, t = 10 \text{ ms})$		V _{DSM} /V _{RSM}	V _{DSM} /V _{RSM} +100	V
Peak Gate Current ($T_J = 125^{\circ}C$, t = 20ms)		I _{gM}	4.0	W
Peak Gate Power (Pulse Width \leq 1.0 µs, T _c = 80°C)		P _{GM}	20	W
Average Gate Power ($T_{J} = 125^{\circ}C$)		P _{G(AV)}	1.0	W
Operating Junction Temperature Range		T,	-40 to +125	°C
Storage Temperature Range		T _{stg}	-40 to +125	°C
RMS Isolation Voltage (t = 300 ms, R.H. \leq 30%, T _A = 25°C)		V _{iso}	2500	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied.

Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability. 1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Thermal Characteristics						
Rating]	Symbol	Value	Unit		
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R _{ejc} R _{eja}	2.5 60	°C/W		
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds		TL	260	°C		

Electrical Characteristics - OFF (T = 25°C unless otherwise noted ; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T ₁ = 25°C	I _{DRM} ,	-	-	0.005	m (
$(V_{D} = V_{DRM} = V_{RRM}; Gate Open)$	T_ = 125°C	I _{RRM}	-	-	2.0	mA

Electrical Characteristics - **ON** ($T_J = 25^{\circ}C$ unless otherwise noted; Electricals apply in both directions)

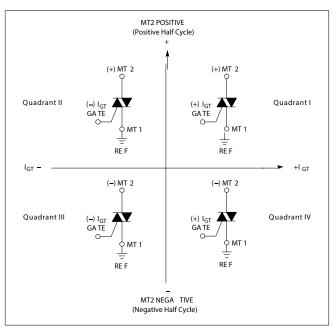
Characteristic		Symbol	Min	Тур	Max	Unit
Forward On-State Voltage (Note 2) ($I_{TM} = \pm 17 \text{ A Peak}$)		V _{TM}	-	-	1.55	V
	MT2(+), G(+)		2.0	-	35	
Gate Trigger Current (Continuous dc) ($V_D = 12 V$, $R_L = 30 \Omega$)	MT2(+), G(-)	I _{GT}	2.0	-	35	mA
	MT2(-), G(-)		2.0	-	35	
Holding Current ($V_p = 12 \text{ V}$, Gate Open, Initiating Current = ±500 mA)		I _H	-	-	50	mA
	MT2(+), G(+)		-	-	60	mA
Latching Current ($V_p = 12 \text{ V}, I_g = 1.2 \times I_{gT}$)	MT2(+), G(-)		-	-	65	
	MT2(-), G(-)		_	-	60	
	MT2(+), G(+)		0.5	-	1.7	
Gate Trigger Voltage ($V_D = 12 \text{ V}, \text{ R}_L = 30 \Omega$)	MT2(+), G(-)	V _{gt}	0.5	-	1.1	V
	MT2(-), G(-)		0.5	-	1.1	
	MT2(+), G(+)		0.2	-	-	
Gate Non-Trigger Voltage (T _j = 125°C)	MT2(+), G(-)	V_{gD}	0.2	-	-	V
	MT2(-), G(-)		0.2	-	-	

2. Indicates Pulse Test: Pulse Width \leq 2.0 ms, Duty Cycle \leq 2%.

Dynamic Characteristics					
Characteristic	Symbol	Min	Тур	Мах	Unit
Rate of Change of Commutating Current, See Figure 9. (Gate Open, T _J = 125°C, No Snubber)	(dl/dt)c	8.5	-	-	A/ms
Critical Rate of Rise of On–State Current ($T_J = 125^{\circ}C$, f = 120 Hz, $I_g = 2 \times I_{gT}$, tr ≤ 100 ns)	dl/dt	-	_	50	A/µs
Critical Rate of Rise of Off-State Voltage ($V_{D} = 0.66 \times V_{DRM'}$ Exponential Waveform, Gate Open, $T_{J} = 125^{\circ}$ C)	dV/dt	1000	_	_	V/µs

Voltage Current Characteristic of SCR

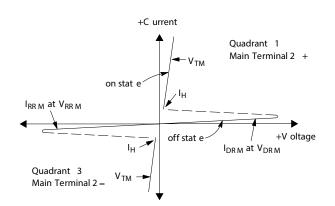
Symbol	Parameter		
V _{DRM}	Peak Repetitive Forward Off State Voltage		
I	Peak Forward Blocking Current		
V _{RRM}	Peak Repetitive Reverse Off State Voltage		
I	Peak Reverse Blocking Current		
V _{TM}	Maximum On State Voltage		
I _H	Holding Current		



Quadrant Definitions for a Triac

All polarities are referenced to MT1.

With in -phase signals (using standard AC lines) quadrants I and III are used



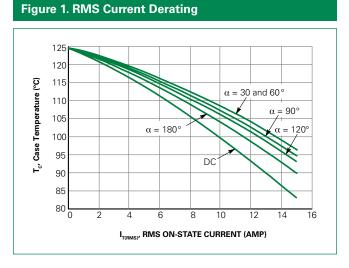


Figure 3. On–State Characteristics

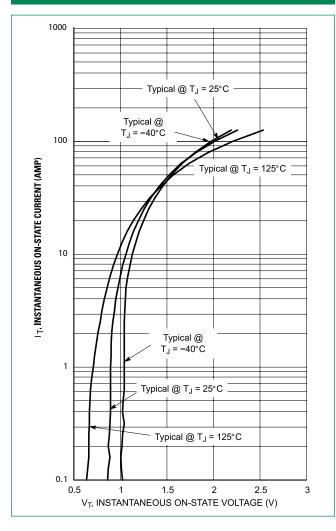


Figure 2. On-State Power Dissipation

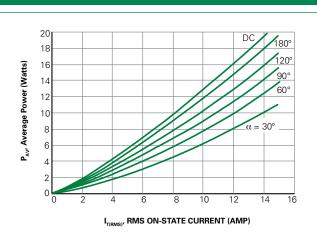


Figure 4. Thermal Response

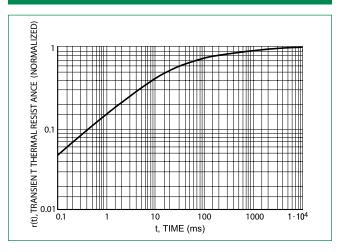


Figure 5. Hold Current Variation

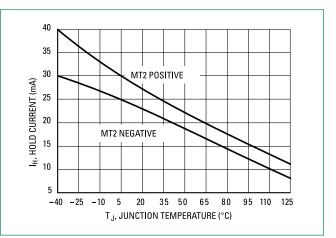
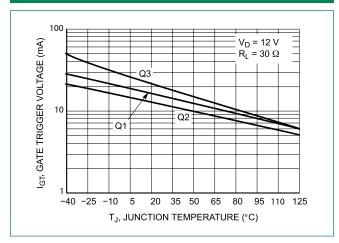


Figure 6. Gate Trigger Current Variation

Littelfuse

Expertise Applied | Answers Delivered



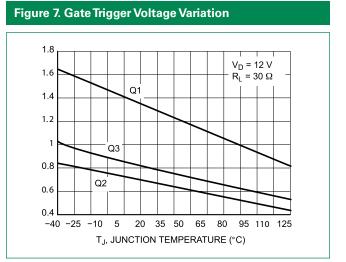
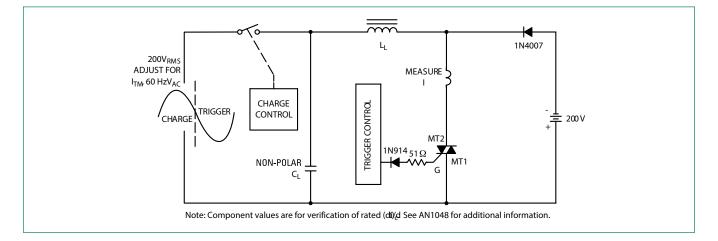


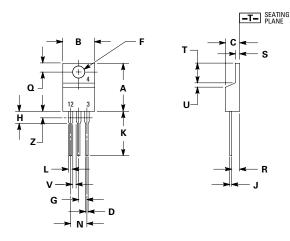
Figure 9. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)



Dimensions

.ittelfuse°

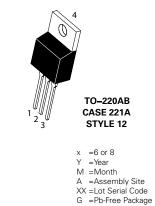
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Part Marking System

S

.1





Dim	Inches		Millin	neters	
Dim	Min	Мах	Min	Max	
Α	0.590	0.620	14.99	15.75	
В	0.380	0.420	9.65	10.67	
С	0.178	0.188	4.52	4.78	
D	0.025	0.035	0.64	0.89	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.41	2.67	
Н	0.110	0.130	2.79	3.30	
J	0.018	0.024	0.46	0.61	
К	0.540	0.575	13.72	14.61	
L	0.060	0.075	1.52	1.91	
Ν	0.195	0.205	4.95	5.21	
٥	0.105	0.115	2.67	2.92	
R	0.085	0.095	2.16	2.41	
S	0.045	0.060	1.14	1.52	
т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

Pin Assignment				
1 Main Terminal 1				
2	Main Terminal 2			
3	Gate			
4	No Connection			

Ordering Information					
Device	Package	Shipping			
BTA16-600CW3G	TO-220AB (Pb-Free)	500 Units / Rail			
BTA16-800CW3G	TO-220AB (Pb-Free)	500 Units / Rail			

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: INCH.

3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

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